

NP061A1

Silicon PNP epitaxial planar transistor

For digital circuits

■ Features

- Two elements incorporated into one package
- Suitable for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

■ Basic Part Number of Element

- UNR31A1 × 2 elements

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Rating of element	Collector-base voltage (Emitter open)	V_{CBO}	-50	V
	Collector-emitter voltage (Base open)	V_{CEO}	-50	V
	Collector current	I_C	-80	mA
Overall	Total power dissipation *	P_T	125	mW
	Junction temperature	T_j	125	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

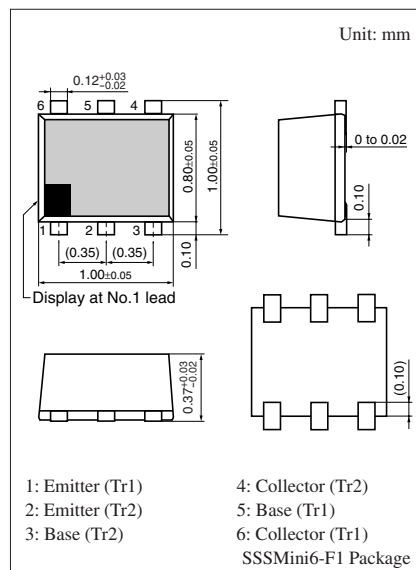
Note) *: Measuring on substrate at 17 mm × 10 mm × 1 mm

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10\ \mu\text{A}$, $I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2\ \text{mA}$, $I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50\ \text{V}$, $I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50\ \text{V}$, $I_B = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6\ \text{V}$, $I_C = 0$			-0.5	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10\ \text{V}$, $I_C = -5\ \text{mA}$	35			—
h_{FE} Ratio *	$h_{FE(\text{Small}/\text{Large})}$	$V_{CE} = -10\ \text{V}$, $I_C = -5\ \text{mA}$	0.5	0.99		—
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -10\ \text{mA}$, $I_B = -0.3\ \text{mA}$			-0.25	V
Output voltage high level	V_{OH}	$V_{CC} = -5\ \text{V}$, $V_B = -0.5\ \text{V}$, $R_L = 1\ \text{k}\Omega$	-4.9			V
Output voltage low level	V_{OL}	$V_{CC} = -5\ \text{V}$, $V_B = -2.5\ \text{V}$, $R_L = 1\ \text{k}\Omega$			-0.2	V
Input resistance	R_1		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	R_1 / R_2		0.8	1.0	1.2	—
Transition frequency	f_T	$V_{CB} = -10\ \text{V}$, $I_E = 1\ \text{mA}$, $f = 200\ \text{MHz}$		80		MHz

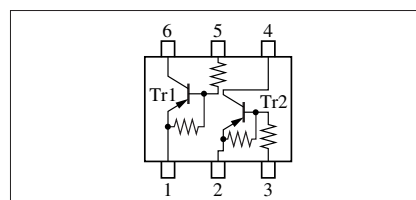
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

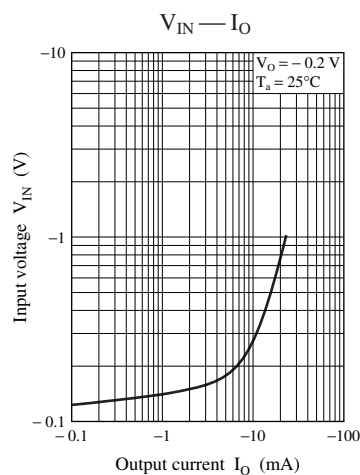
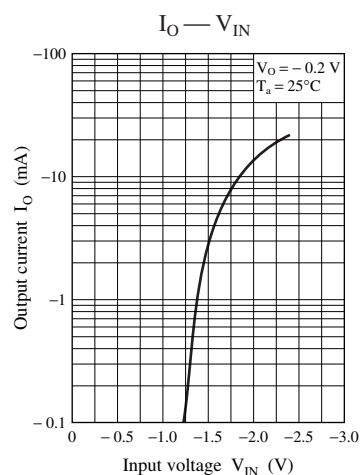
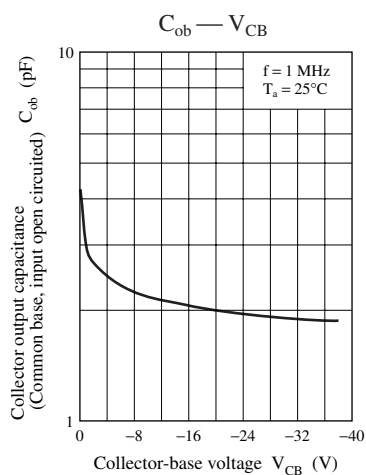
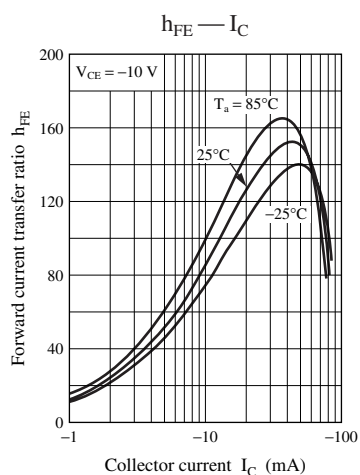
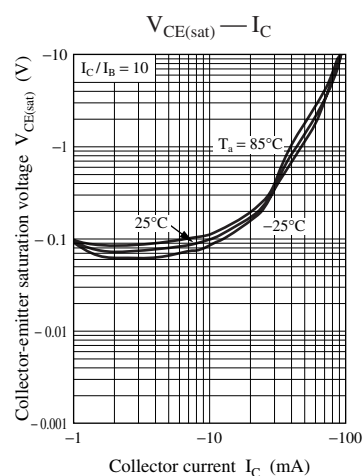
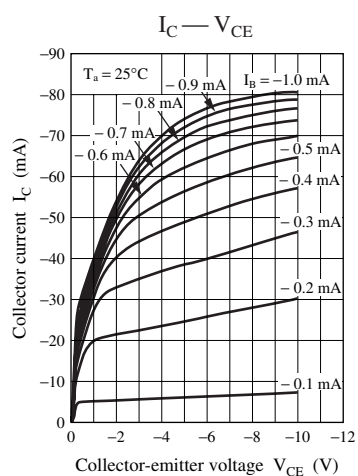
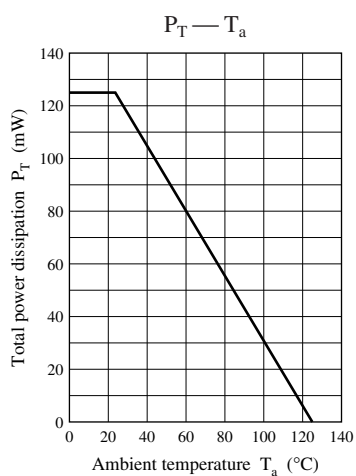
2. *: Ratio between one and another



Marking Symbol: 5Z

Internal Connection





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